

Designing Atomic Level Process Chemistries: The Role of Atomistic Simulation in Developing Sustainable Deposition and Etch Processes

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Materials Modelling for Devices Group



Materials Modelling for Devices Members and Atomic Level Processing Research Directions

Michael Nolan (Head of Group/Tyndall interim Chief Scientist, MMD-MNS)

ALD/ALE of Oxides, Metals, Nitrides, Hybrid Materials, Polymers
Materials Discovery

Ji Liu (MMD-MNS)

ALD of Oxides, Metals, Nitrides
Precursor Chemistry

Arbresha Muriqi (MMD-MNS)

Hybrid Materials MLD and VPI
Precursor Chemistry
Interfaces

Rita Mullins (MMD-MNS)

Atomic Layer Etching of Oxides,
Metal ALD

Alessandra Imbrogno (MMD-MNS)

MLD of Polymers, ALD of Nitrides

New in 2024: Postdoc on kMC, PhD & MSc on ALE

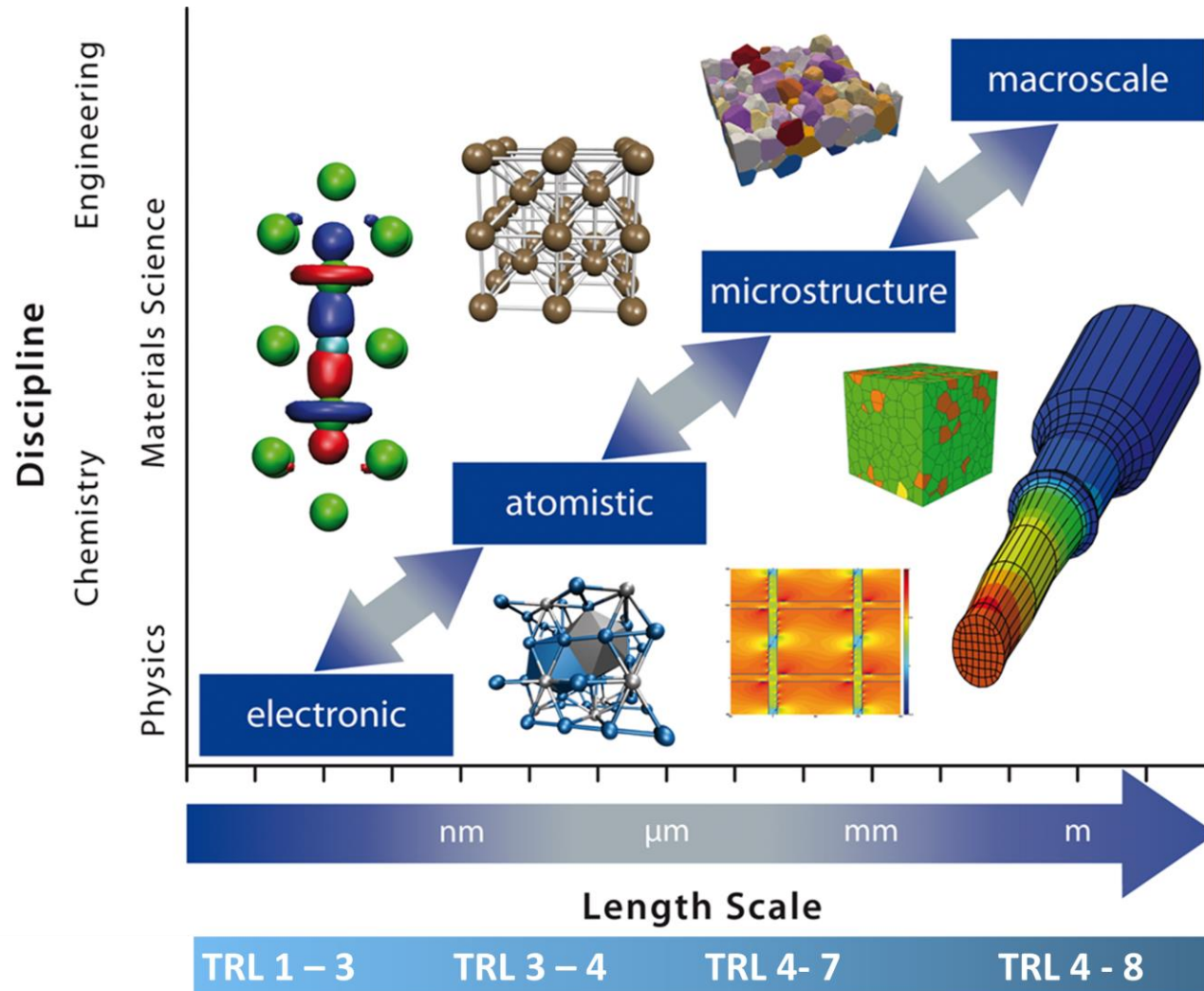


Tyndall 4000 CPU Core High Performance Computing Cluster

**Irish Centre for High End Computing (Tier-2)
National Service, 13600 CPU Core – 40x upgrade in
2024 through EuroHPC**

**EuroHPC Tier-2 Service: e.g LUMI, LEONARDO,
Mare Nostrum, VEGA, ...**

Introduction to Atomic-Scale Simulation and Modelling



Mathematical Description of phenomena

electronic
atomistic
structural
devices
processing
wave propagation

Range of Length and Timescales

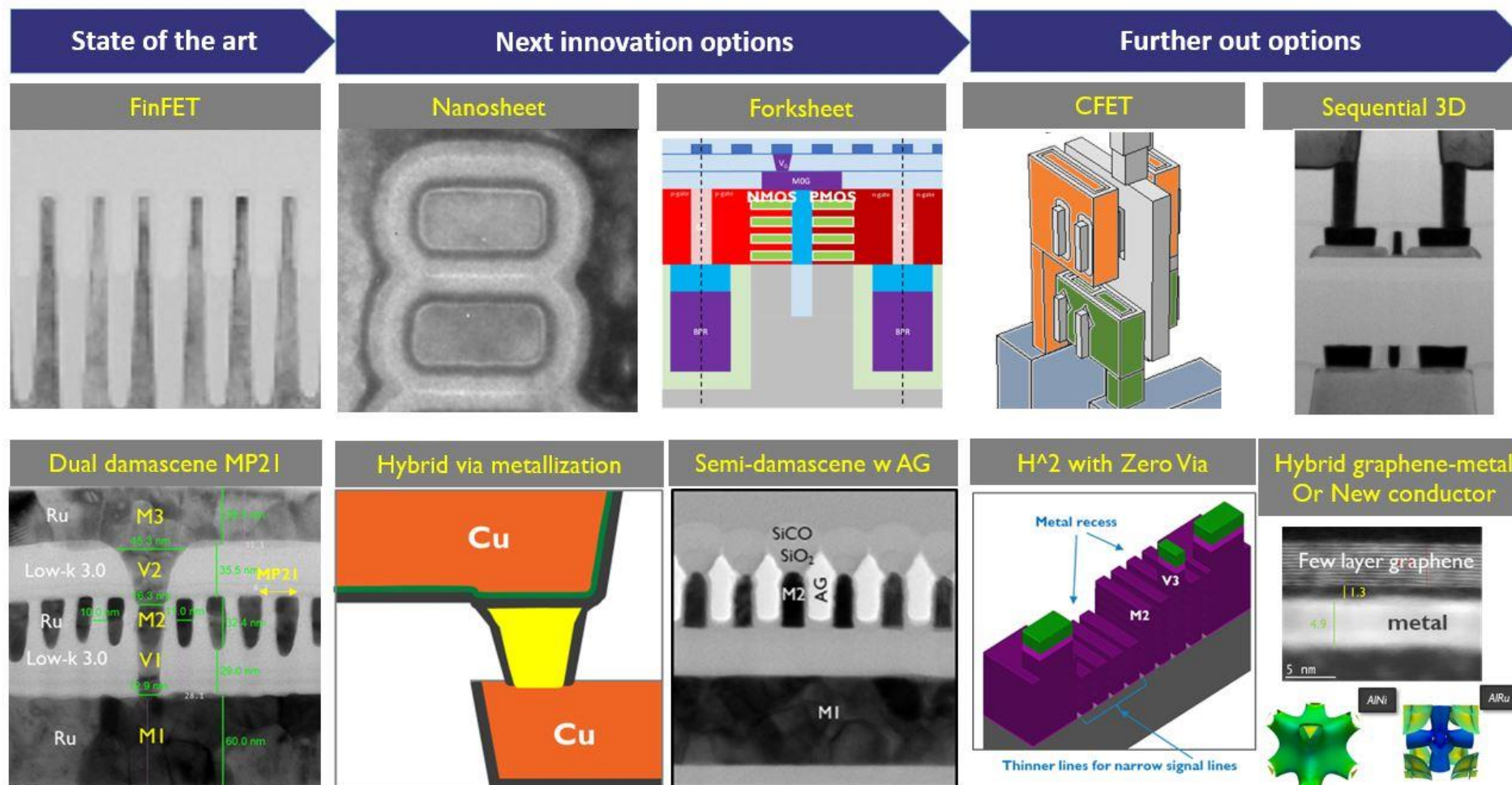
$10^{-15} - 10^{-12} \text{ s} / 10^{-9} \text{ m}$

$10^{-9} - 10^{-3} \text{ s} / 10^{-9} - 10^{-6} \text{ m}$

$10^{-3} - 10^6 \text{ s} / 1 - 10^3 \text{ m}$

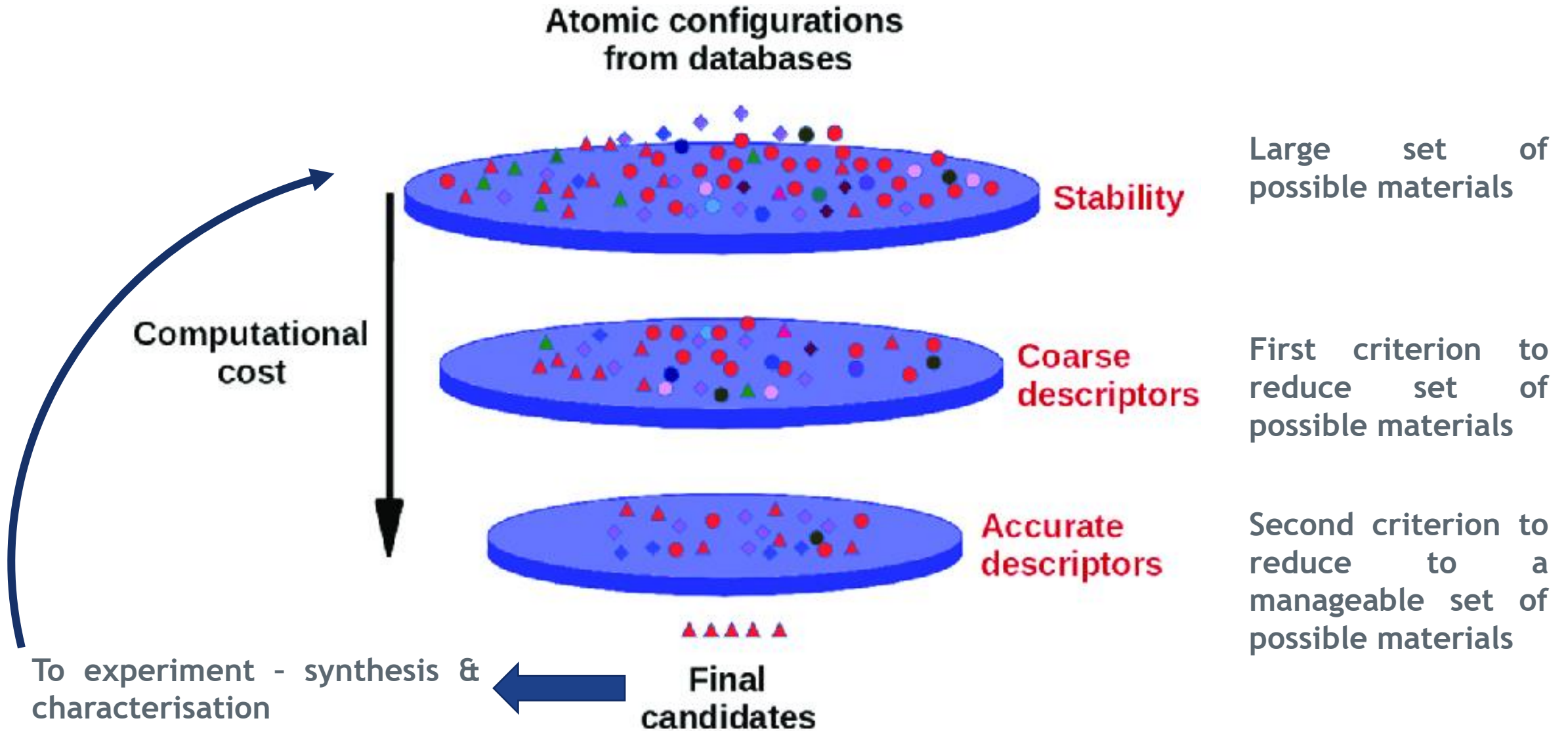
**Coarsening of Information upon
increasing length scale**

Why is atomic level simulation so important?

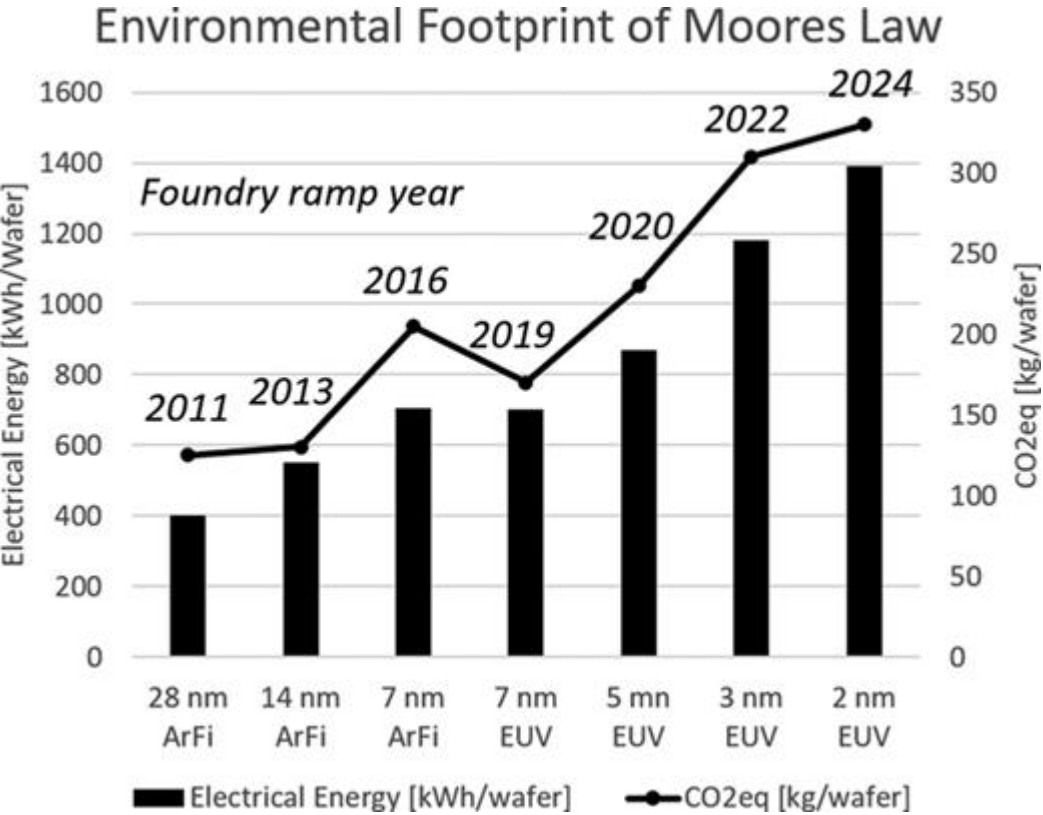


An imec view on the CMOS technology scaling roadmap.

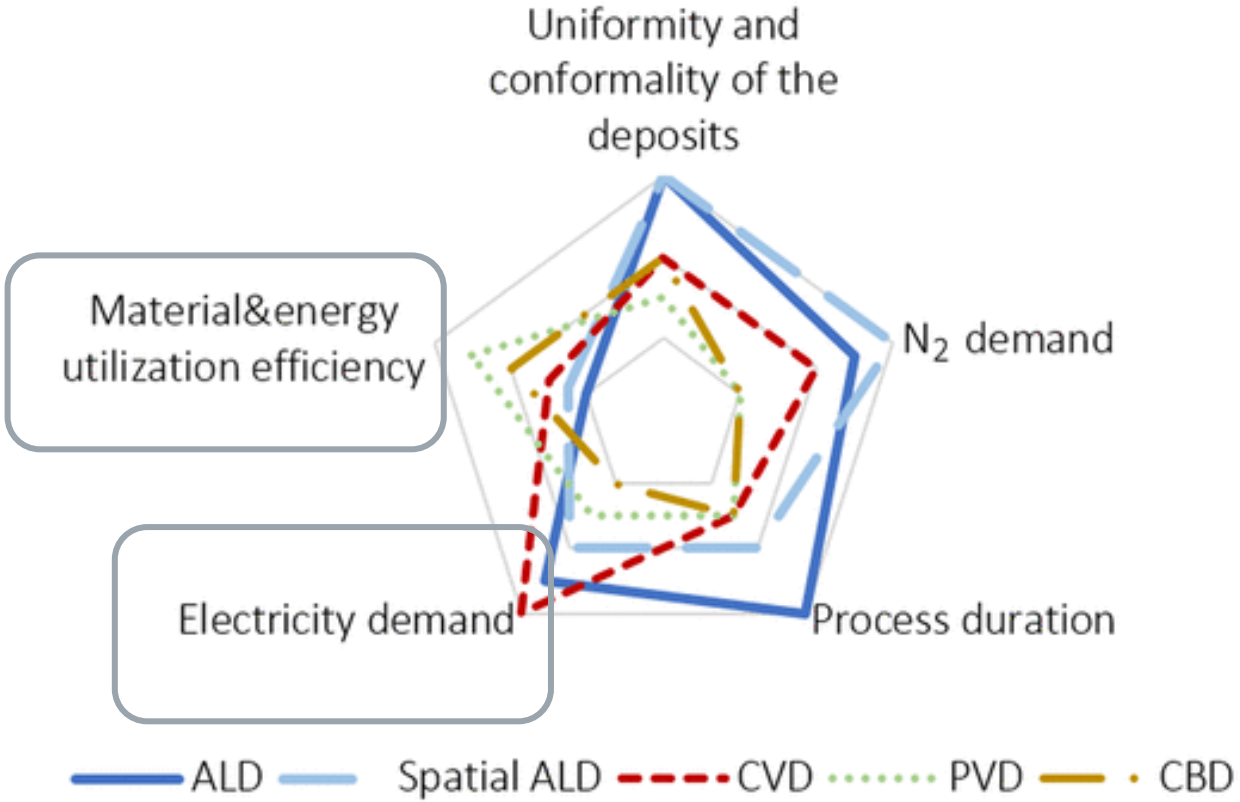
Computational Materials Screening



Sustainability Challenges in Atomic Level Processing

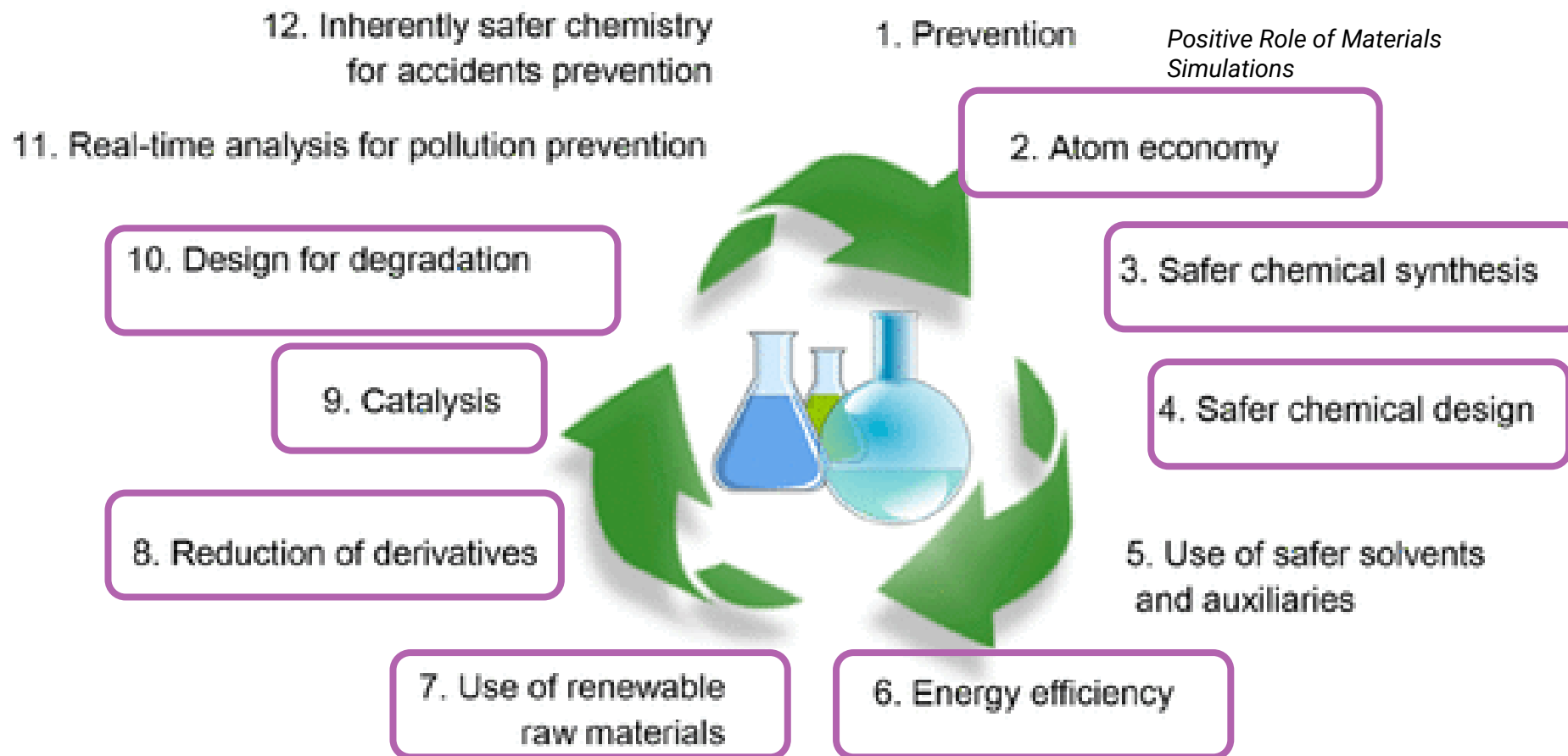


<https://doi.org/10.1116/6.0001125>



Weber et al ACS Mater Au 2023, 3, 274

Principles and Green/Sustainable Chemistry

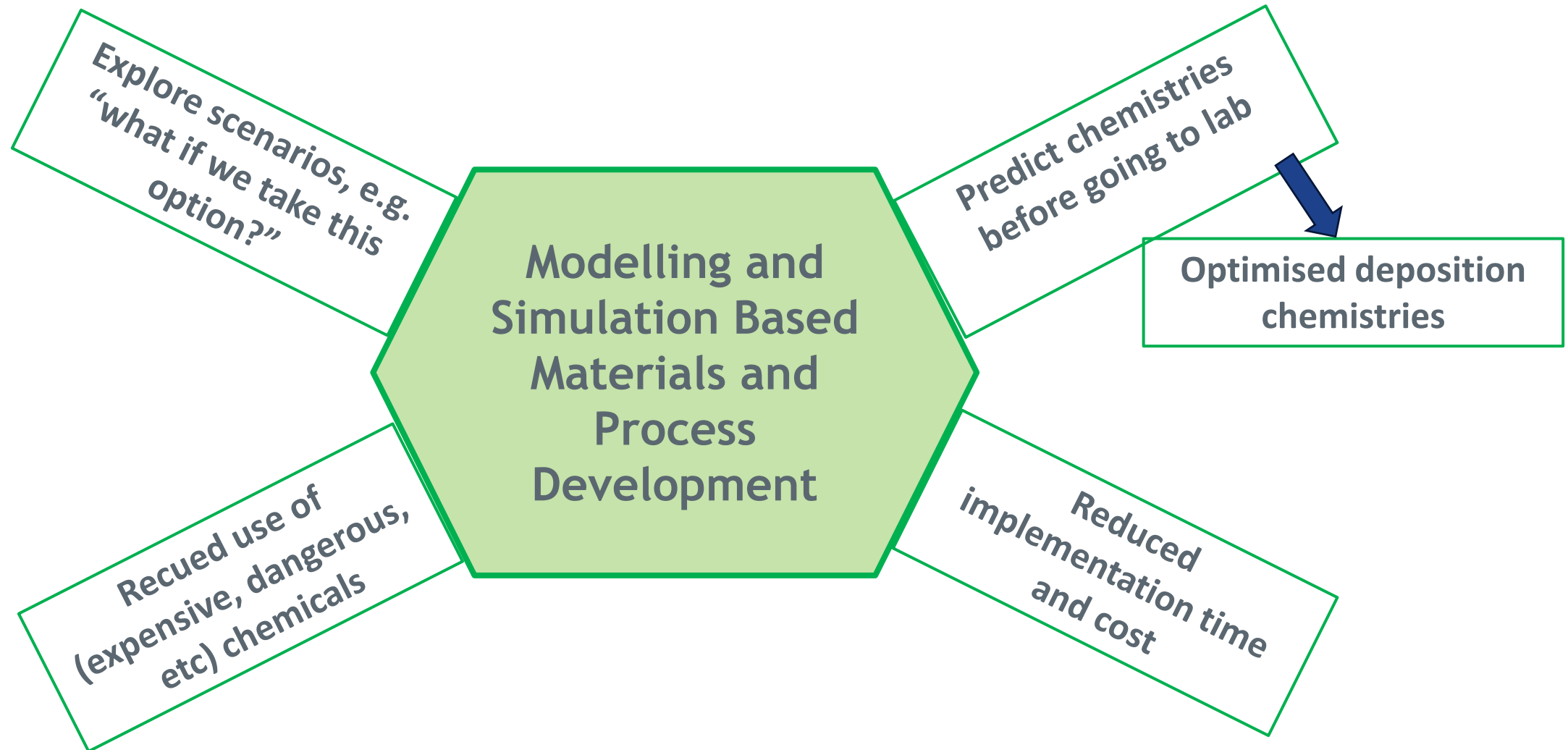


Weber et al ACS Mater Au 2023, 3, 274

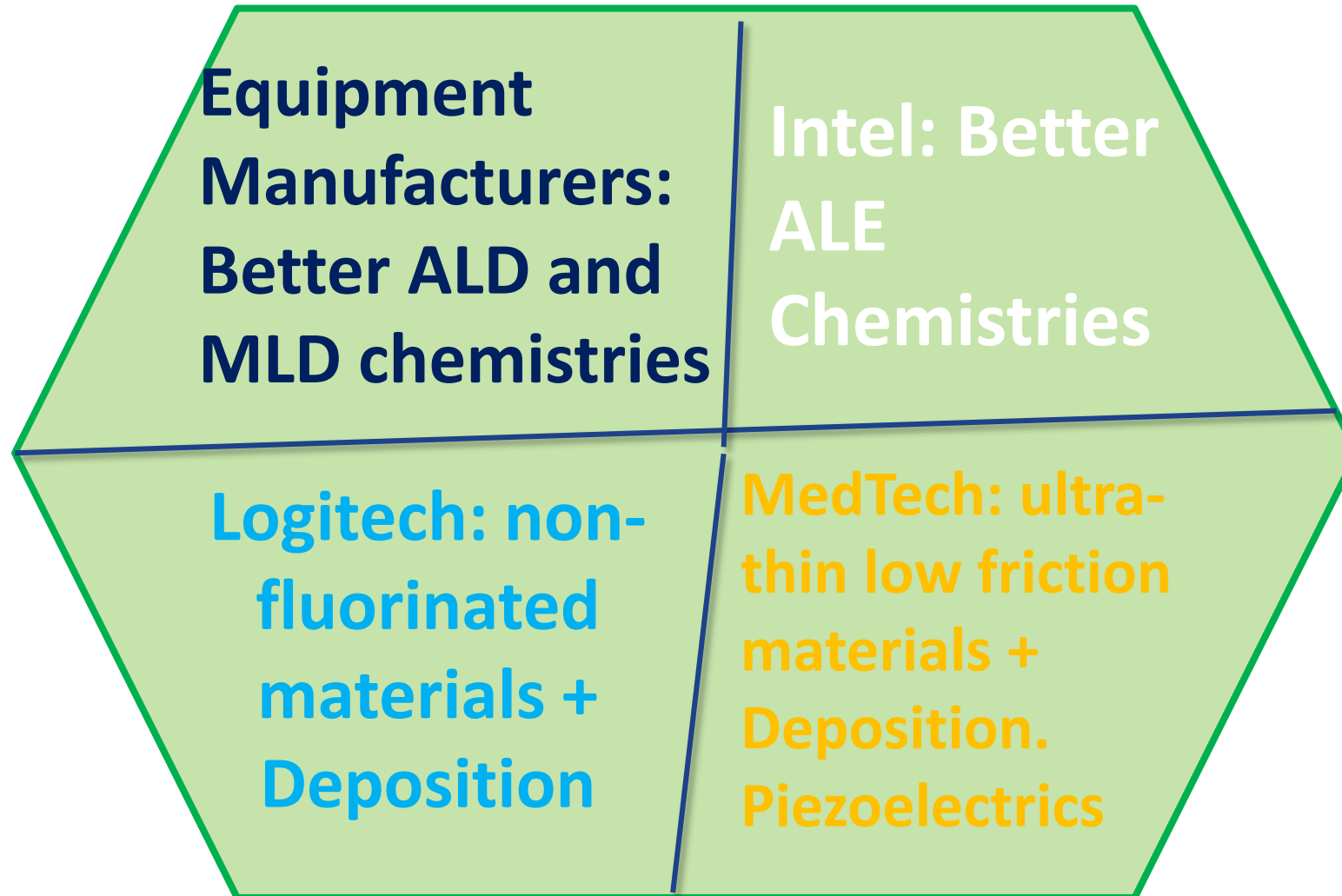
Anastas and Eghbali. *Chem. Soc. Rev.* **2010**, 39 (1), 301– 312, DOI: 10.1039/B918763B

Saudi Pharm. J. **2019**, 27 (1), 1– 8, DOI: 10.1016/j.jsps.2018.07.011

Sustainability Benefits of Simulation



Sustainability Benefits of Simulation



Sustainability Benefits of Simulation

Our Examples:

- “Digital Twin” for ALP development and optimisation
- Processes with less harsh and lower energy intensity chemistries
- Precursors for Atomic and Molecular Layer Deposition

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- Precursors for Atomic and Molecular Layer Deposition
- Replace fluorinated chemicals for etch and other processes
replace halogens for etch

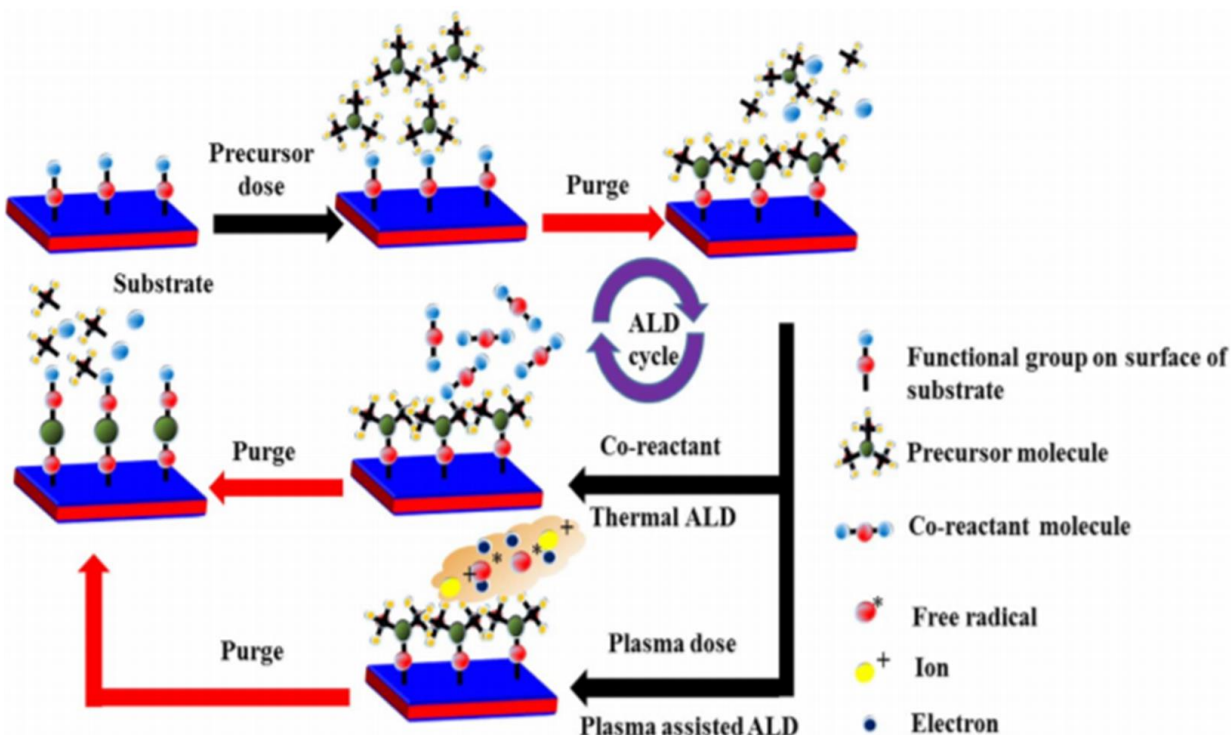
Sustainability Benefits of Simulation

Our Examples:

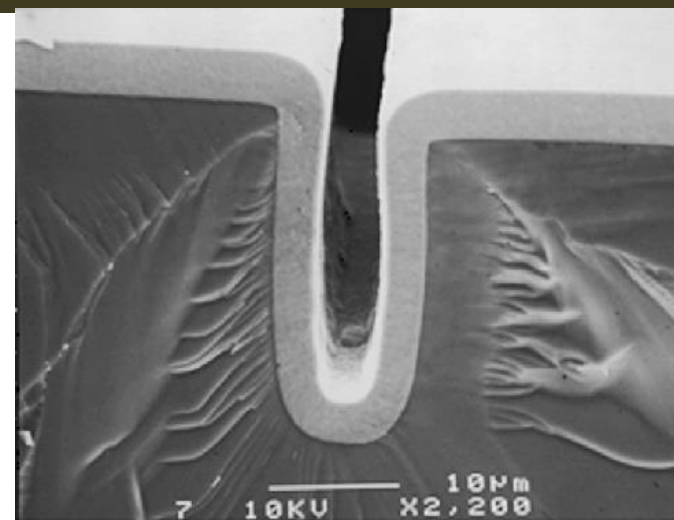
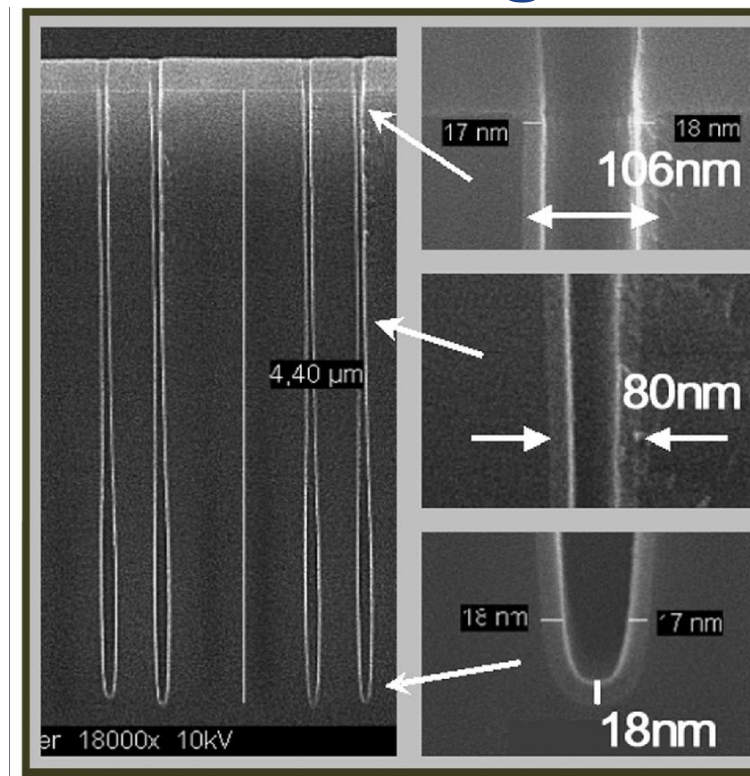
- “Digital Twin” for ALP development and optimisation
- Processes with less harsh and lower energy intensity chemistries
- Precursors for Atomic and Molecular Layer Deposition
- Replace fluorinated chemicals for etch and other processes
replace halogens for etch
- Avoid precious and critical materials
- MLD process chemistry for thin lubricious coatings
- Non-fluorinated low friction coatings for gaming peripherals

Surface Chemistry for Atomic Level Processing

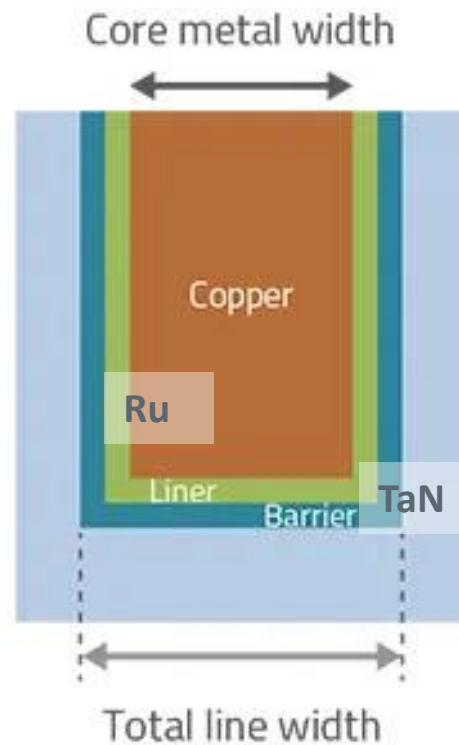
Deposition



Ultra thin coatings
Complex structures
Uniformity (< 1%)
Conformal

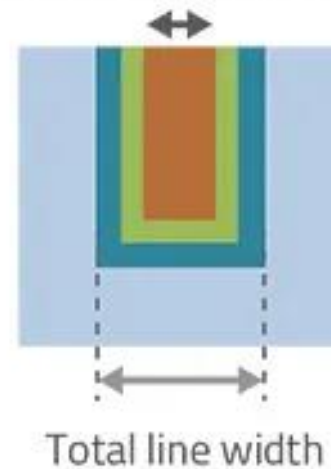


Example – Metal Interconnects



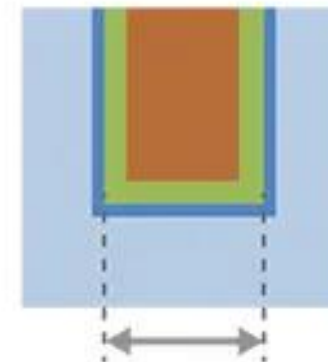
Simple Shrink Leads to Line Resistance Issues

Not enough room for core metal



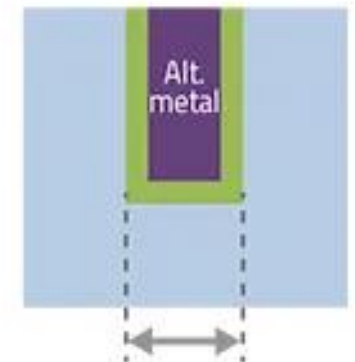
Lower Line Resistance Options

Alternate barrier



Our Solution:
Single Layer
Barrier/Liner

No barrier



**Cobalt as
interconnect metal
– how to deposit?**

ALD of Alternative Interconnect

PE-ALD of Ru and Co with H_2/NH_3 plasma

Precursor reaction mechanism is not clear

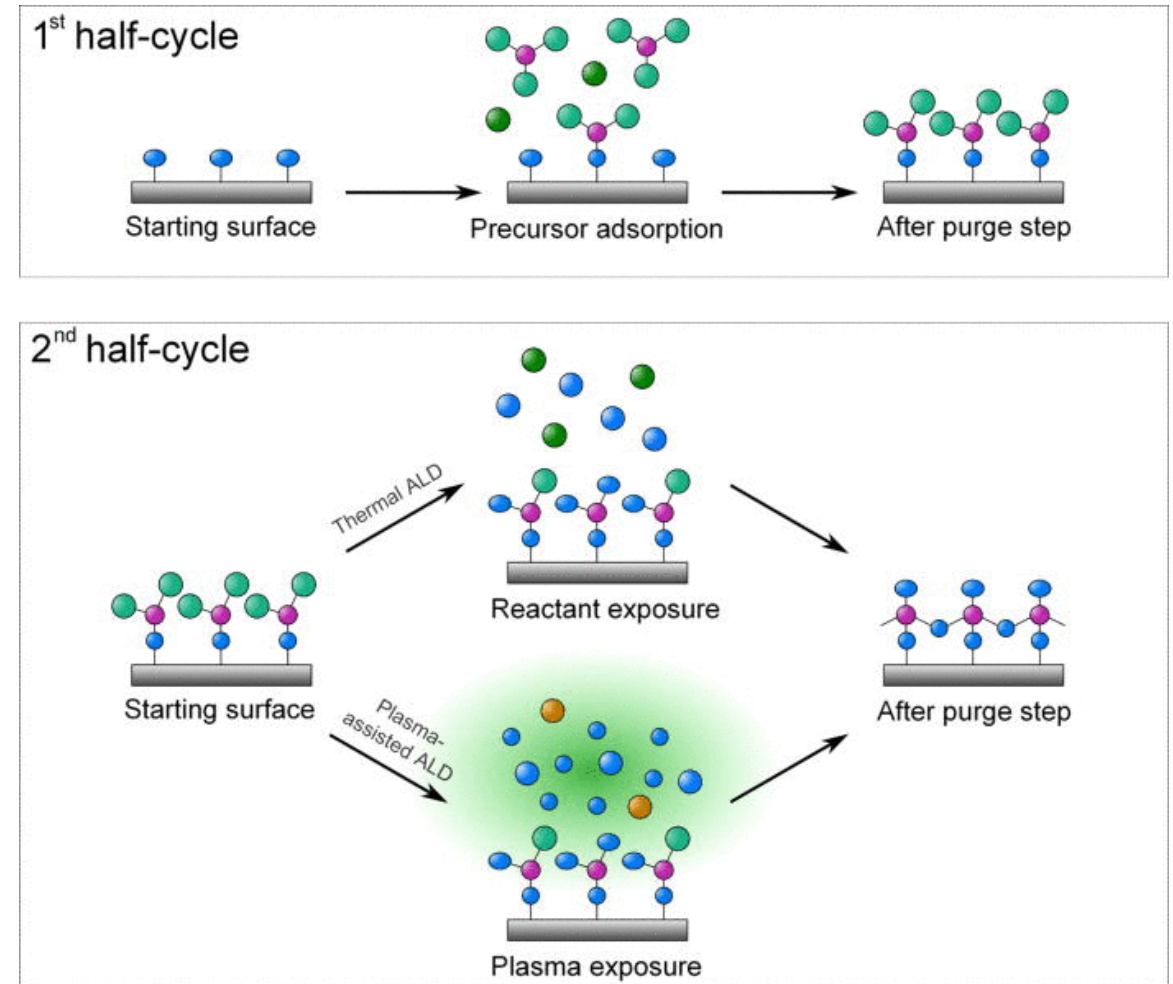
I: coverage and stability of NH_y -terminations

II: precursor reaction mechanism at first half cycle

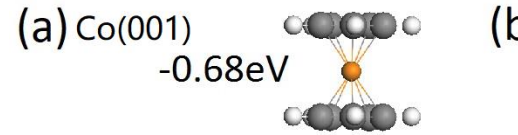
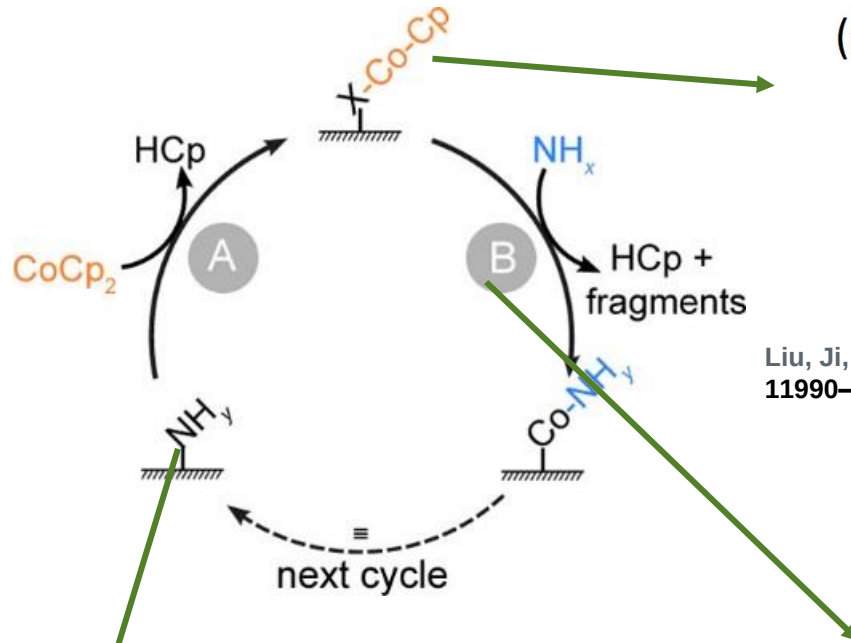
(hydrogen transfer)

III: final structure/termination after metal precursor pulse

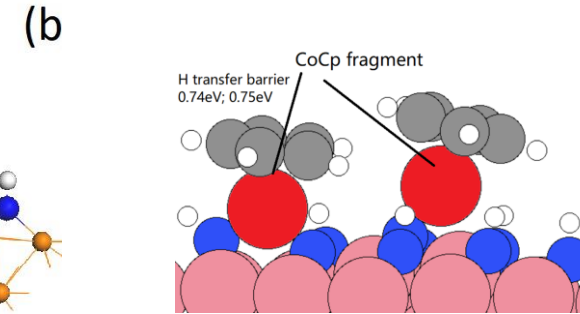
IV: reaction mechanism at second half cycle
(plasma step)



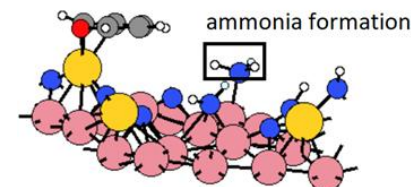
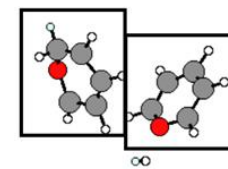
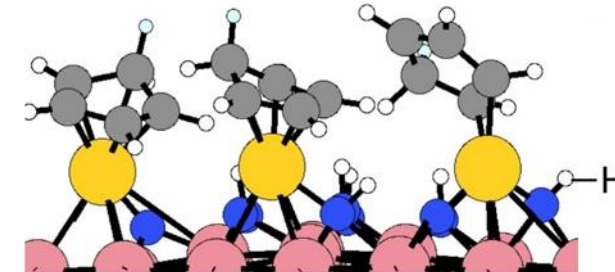
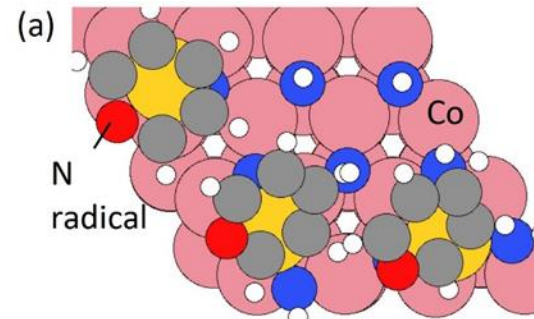
Metal Plasma ALD: First Full ALD Cycle Study



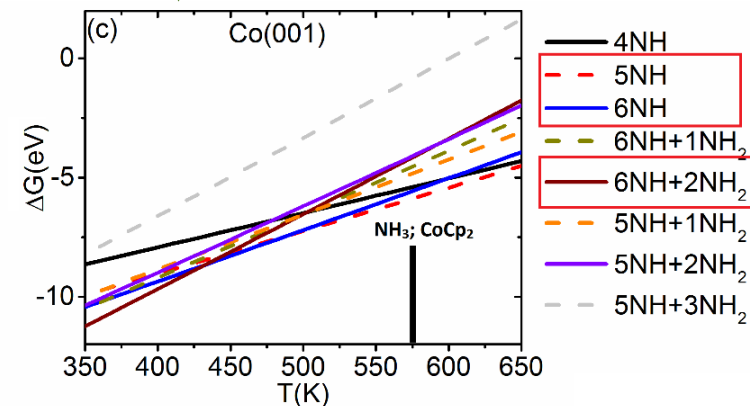
Liu, Ji, et al. *J. Phys. Chem. C* 2020, 124, 22, 11990–12000



Liu, Ji, et al. *J. Mat Chem. C* 2021, 9 2919



Liu, Ji, et al. *Nanoscale* 2022, doi:10.1039/D1NR05568B

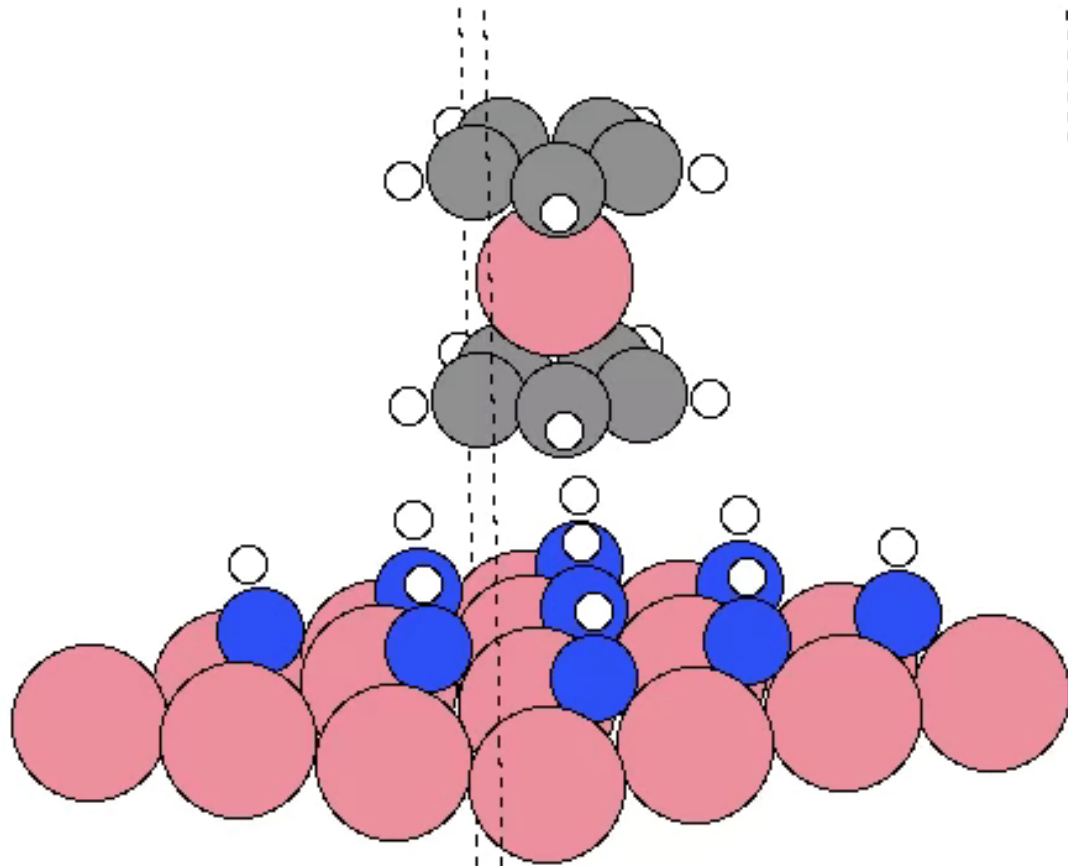


Liu, Ji, and Michael Nolan." *J. Phys. Chem. C* 123.41 (2019): 25166-25175.

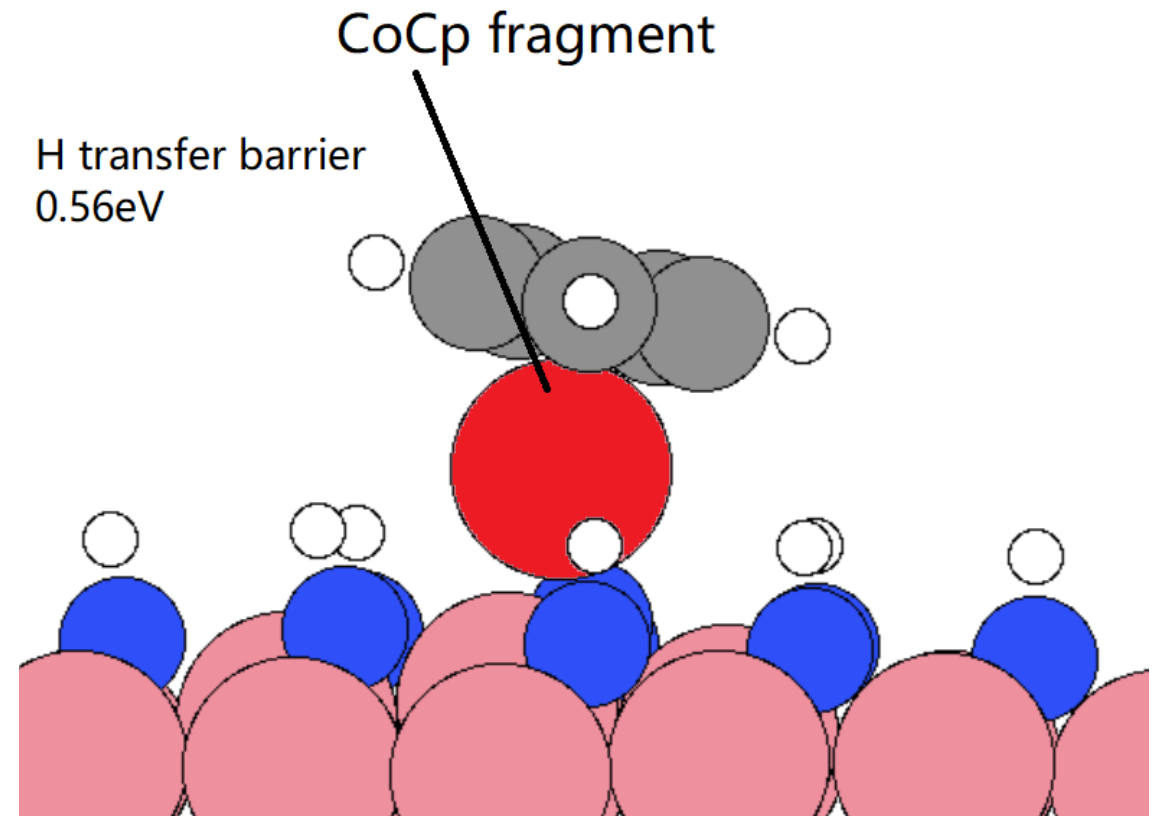
Precursor reaction mechanism

Simulation to predict:

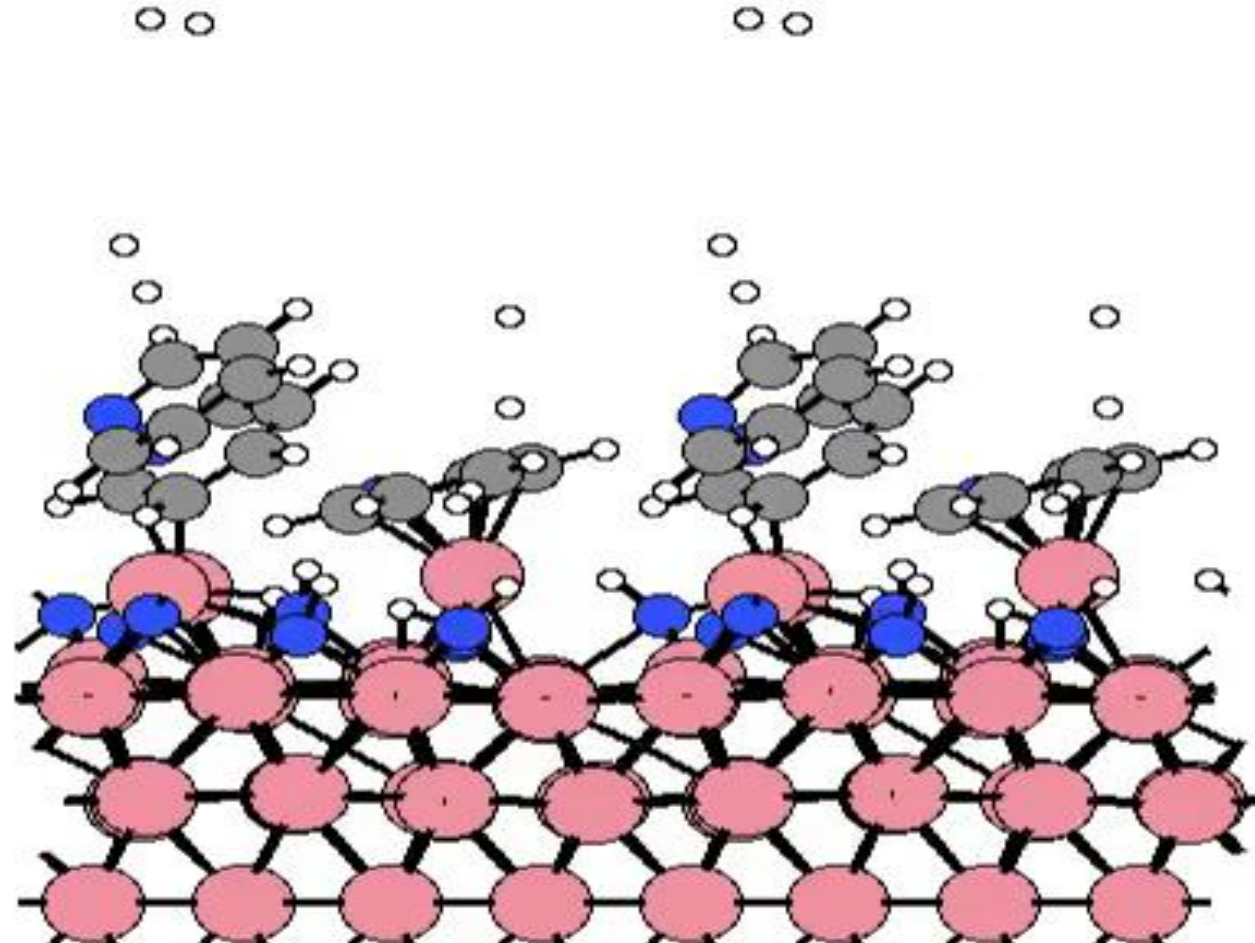
- Thermodynamics of reaction of precursor at surface: *is the possible chemistry favourable?*
- Kinetics: *calculating activation barrier of key process step(s)*
- Screening precursors without doing lab experiments



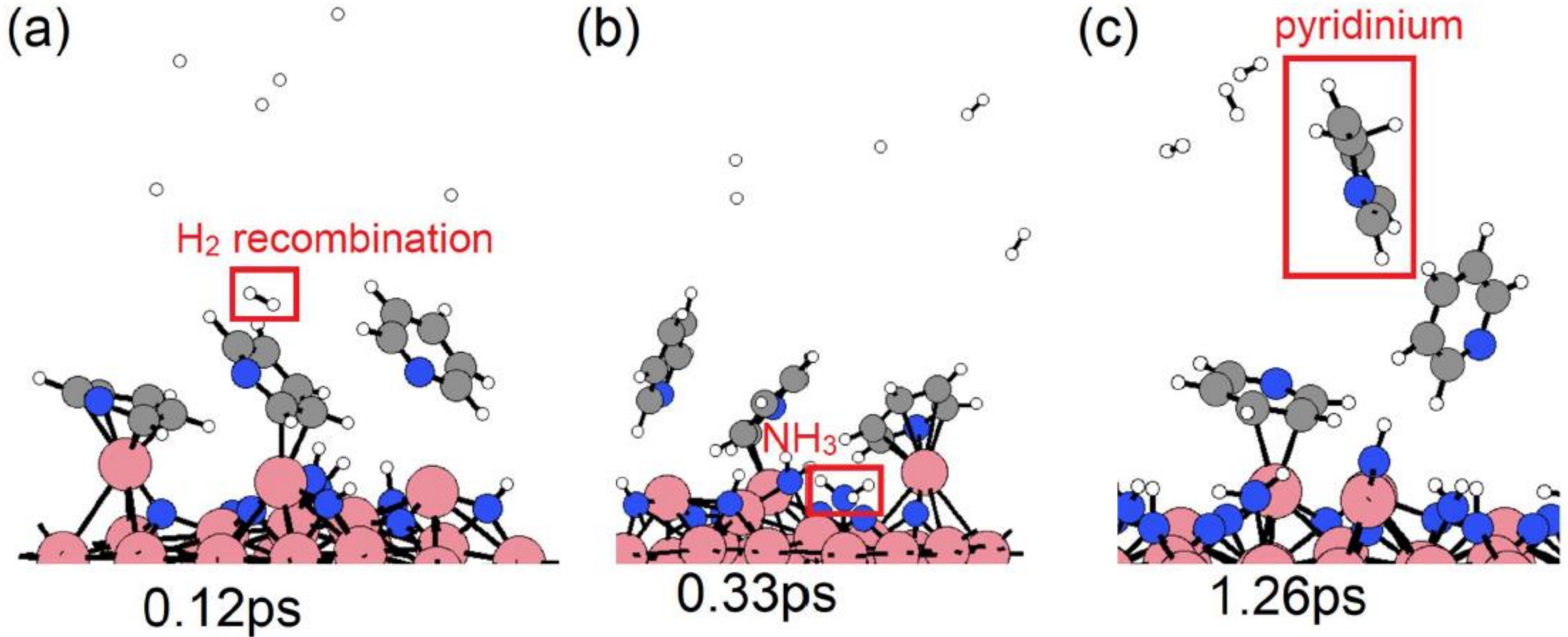
Single CoCp_2



N-plasma half-cycle



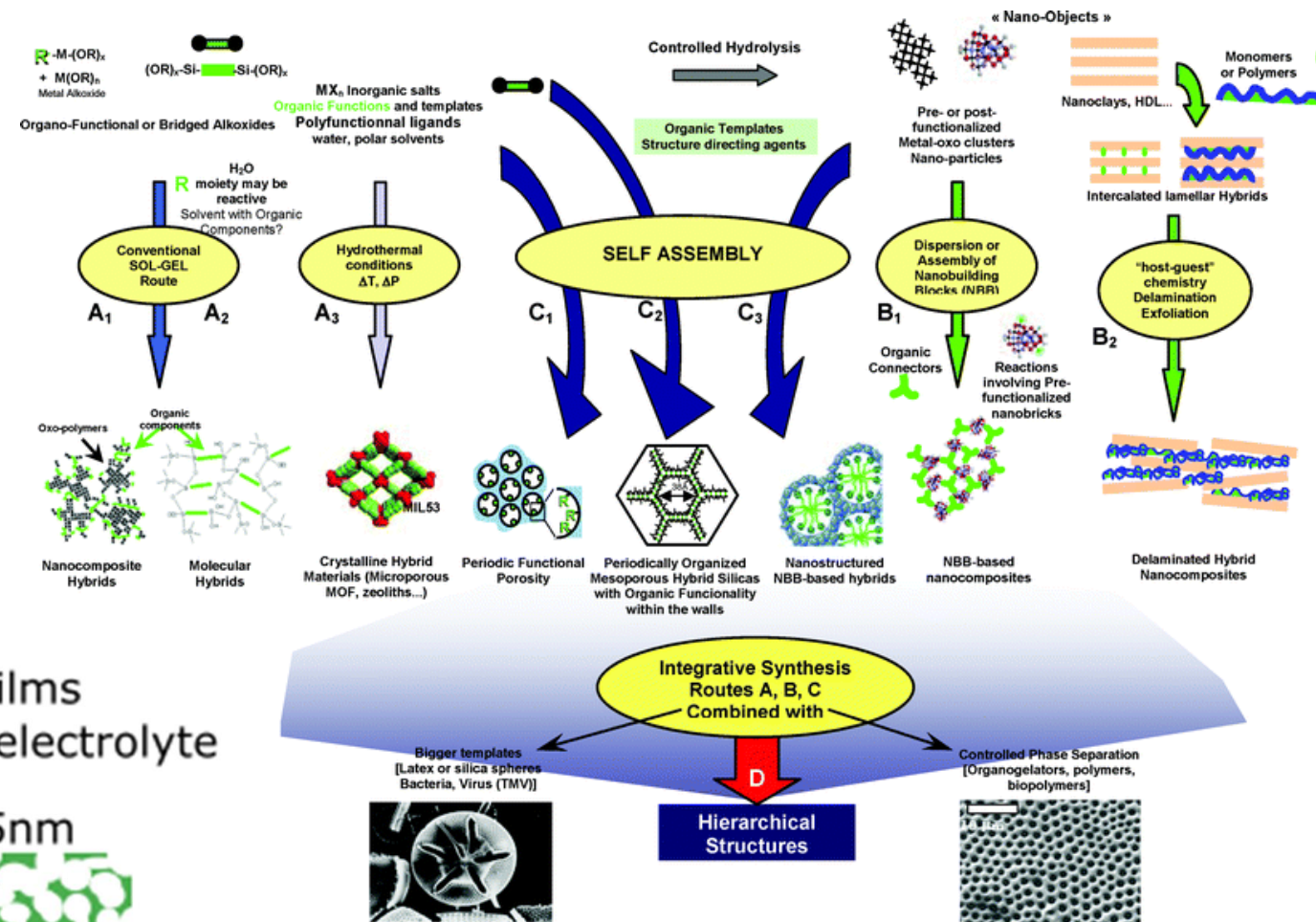
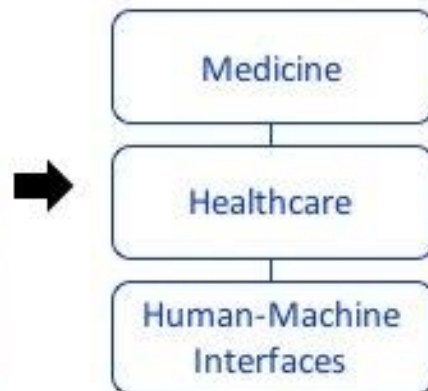
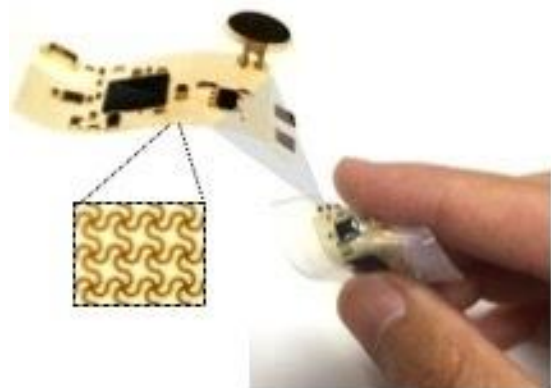
N-plasma half-cycle



Example - Hybrid Polymer/Organic Materials

Hybrid inorganic-organic materials interesting across many technologies

Soft Material-Enabled, Flexible Hybrid Electronics



Moisture barrier

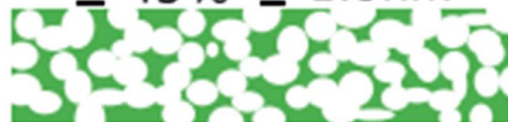


ALD Al₂O₃

MLD magnesicone

Porous MgO films
for solid composite electrolyte

≤ 45% ≤ 1.5nm



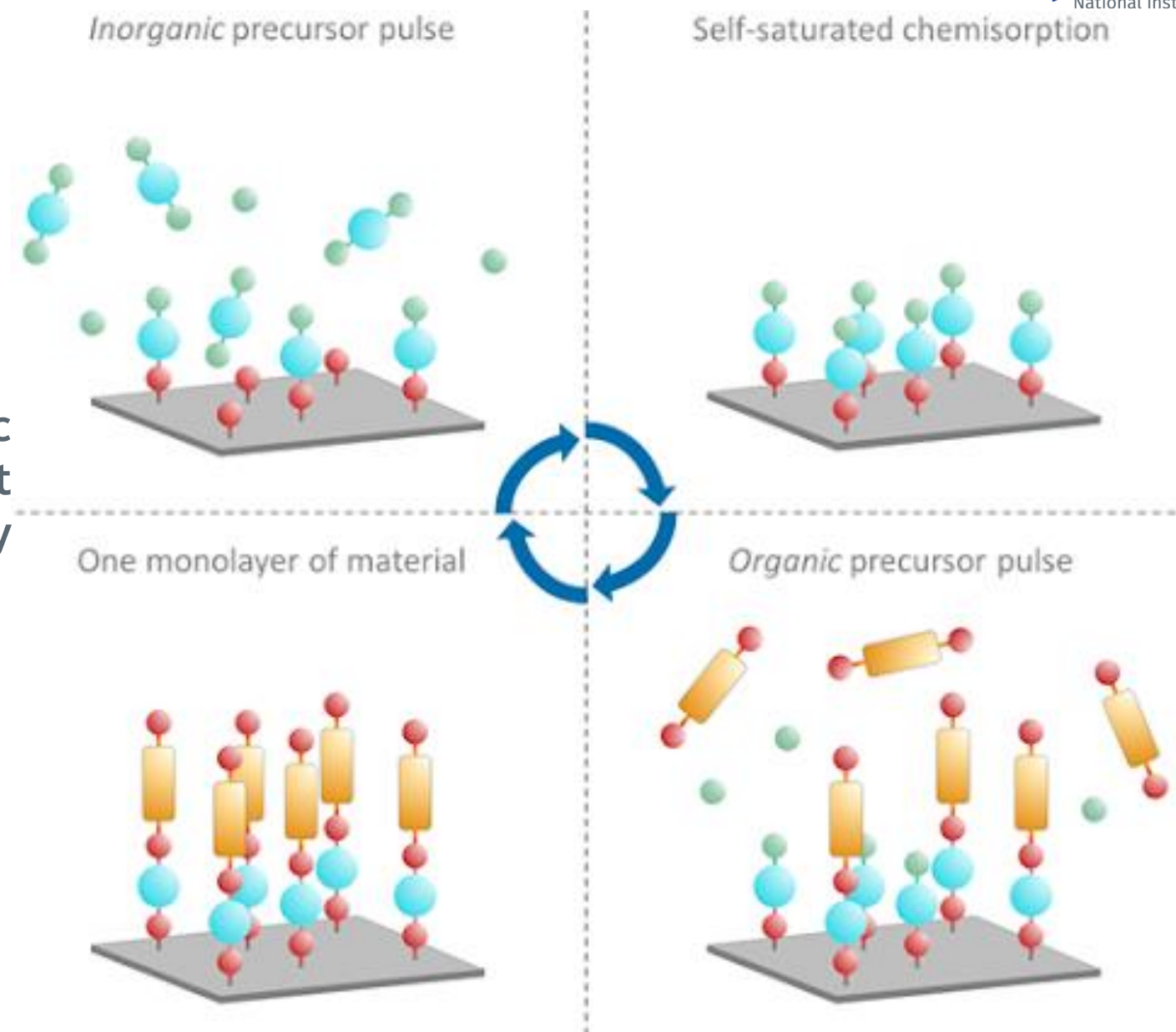
Example - Hybrid Polymer/Organic Materials

Exploit Molecular Layer Deposition

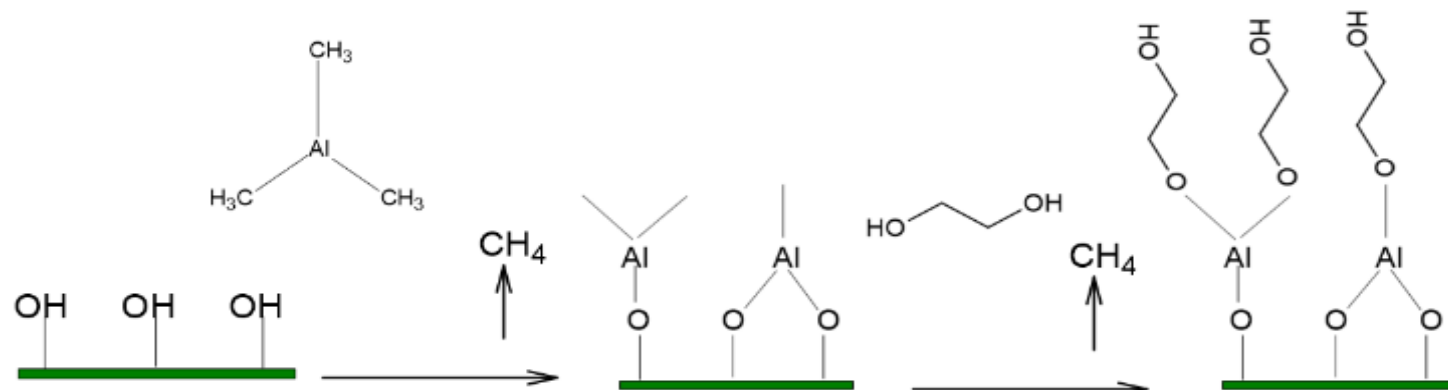
MLD benefits from atomistic simulations to understand/predict chemistries in advance of laboratory work

-> *Eliminate non-performing chemistries*

-> *Avoid unsustainable materials and chemicals*



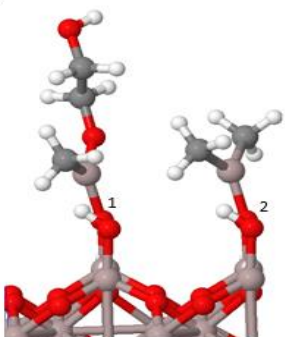
Example - Hybrid Polymer/Organic Materials



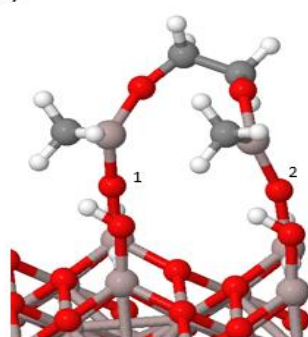
Alucone hybrid film growth

Ethylene Glycol

a)

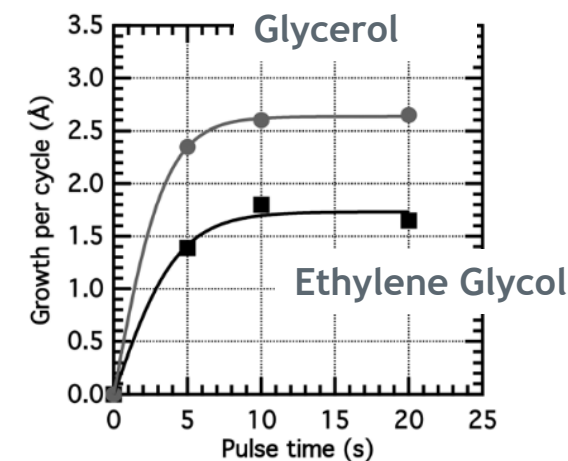
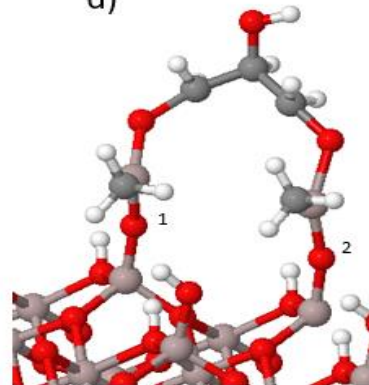


b)



Glycerol

d)



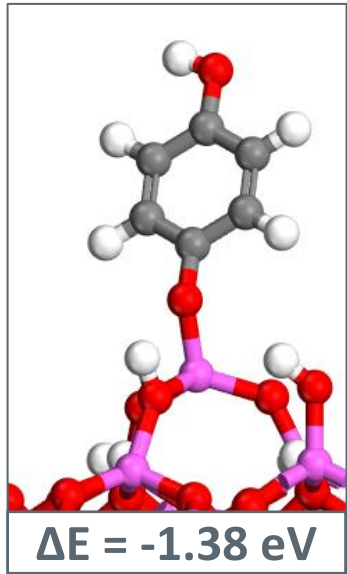
Preference for both to lie flat

Glycerol grows thicker films because it has extra reactive sites
But alucones show poor stability in ambient

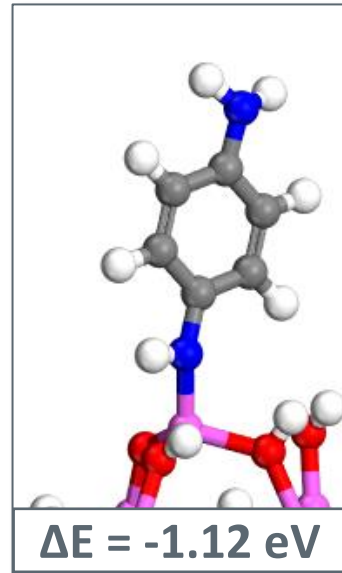


Hybrid Materials

Hydroquinone (HQ)

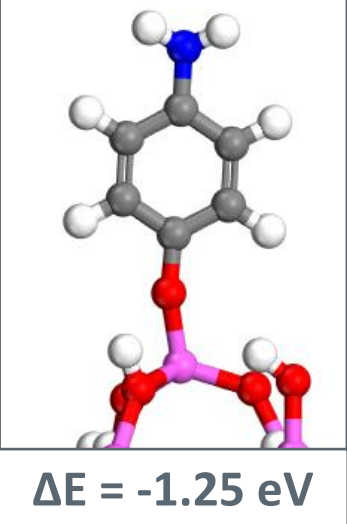


Phenylenediamine (PD)

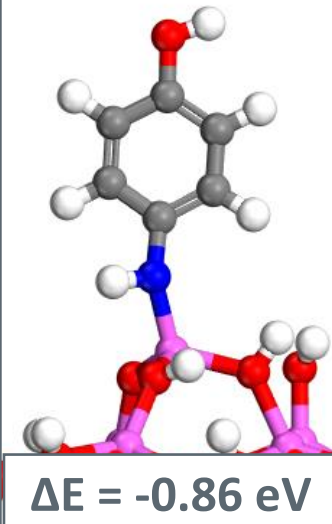


Aminophenol (AP)

AP (Al-O bonding)



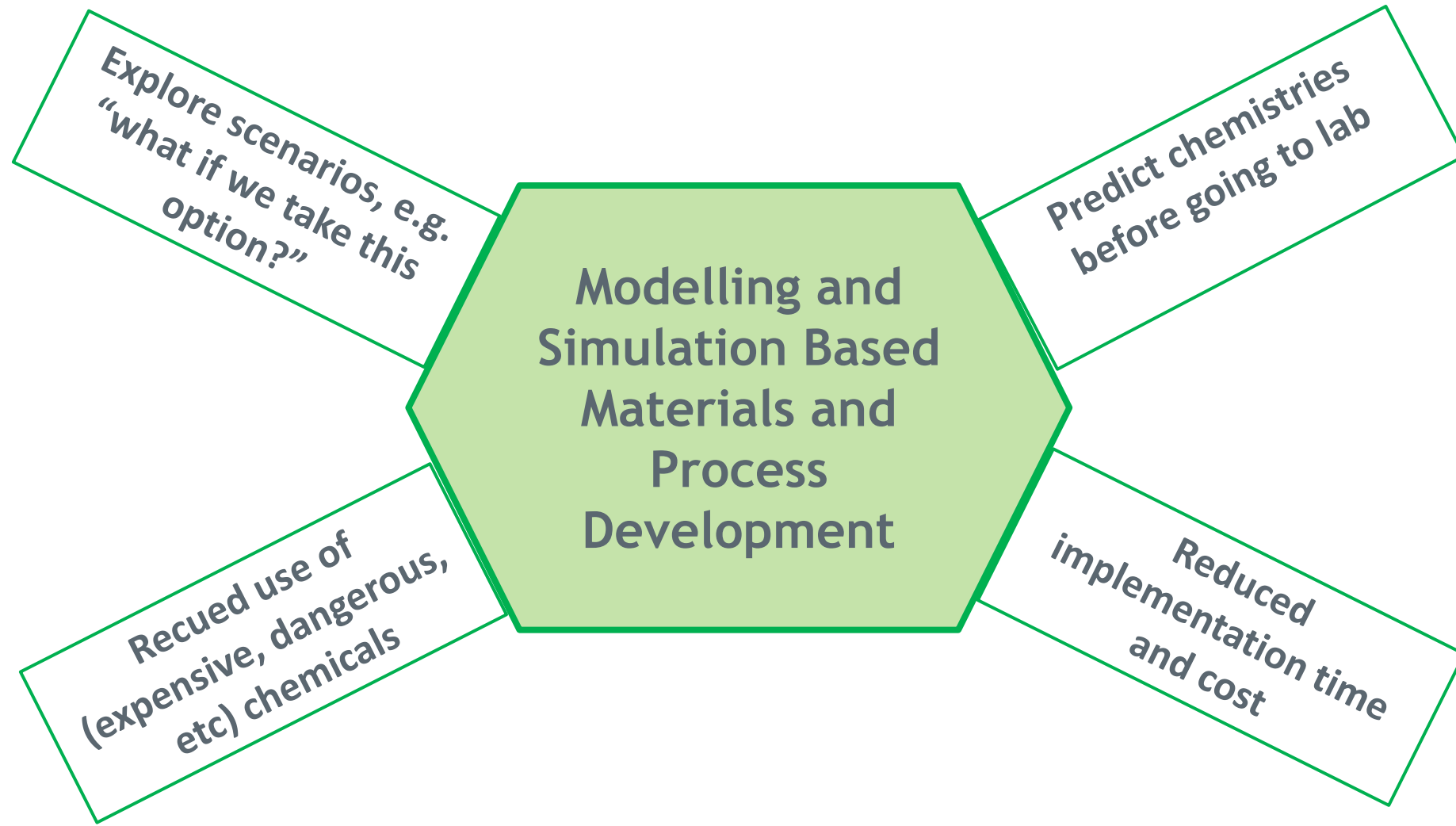
AP (Al-N) bonding



- All aromatic organic precursors react favorably with TMA adsorbed on the Al₂O₃ surface
- The energies indicate that formation of the Al-O bond is more favourable compared to the Al-N bond
- Key result is that the preference is for the upright and rigid configuration
- New class of organics for hybrid materials
- Idea Proved in MLD study with Aalto
- A Tanskanen, P Sundberg, M Nolan, M Karppinen, Thin Solid Films 2021, 736, 138896



Sustainability Benefits of Simulation



BENEFITS

Transnational Access Program: benefit from access & expertise of:



- Opportunities to **collaborate**
- Access to **state-of-the-art equipment** & unique platform technologies of 16 cleanrooms
- **Free-of-charge**

NANOFABRICATION

- Non-standard processing
- Industry-standard and non-standard fabrication
- Innovative materials and devices
- GaN-IC (on-SOI) platform for power electronics and fabrication via MPW shuttles
- Diamond CVD Growth and Nanofabrication, IPMS deposition tools for MRAM-stacks, NVM ferroelectrics, high-k and low-k dielectrics and IZM wafer-level packaging

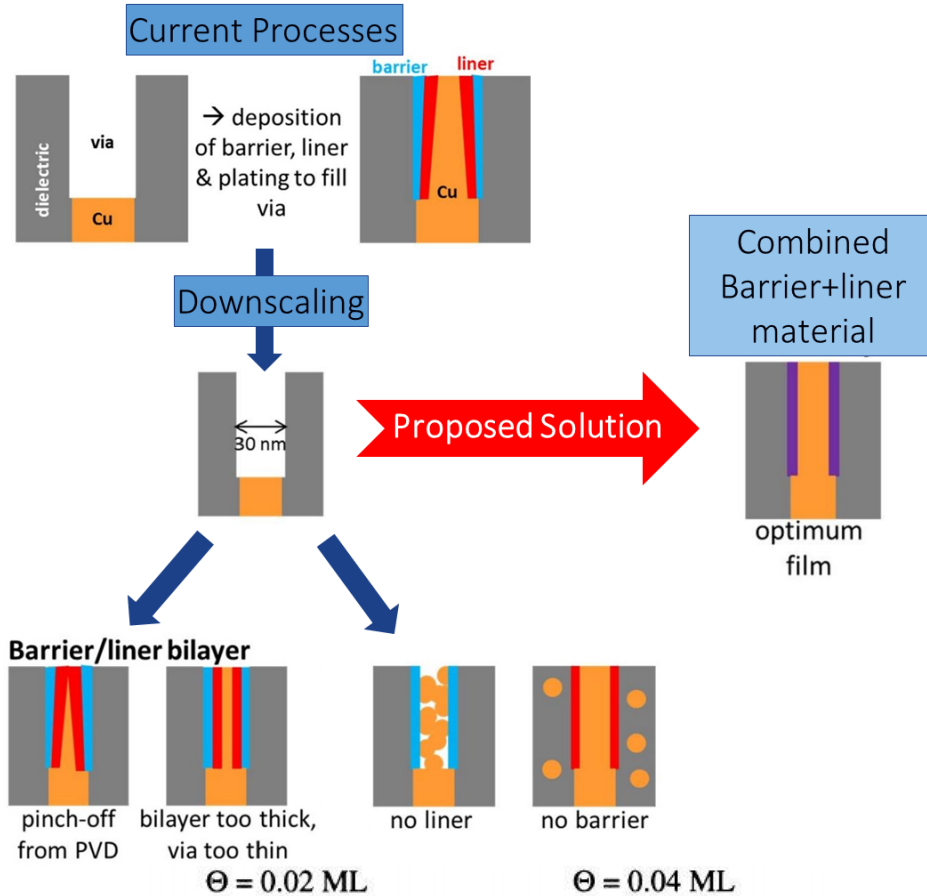
CHARACTERISATION SUITE

- Electrical test labs and device characterisation facilities
- Electron microscopy and spectroscopy
- Electrical test labs and Nano-Characterisation platform capabilities device
- Electrical & physical characterisation

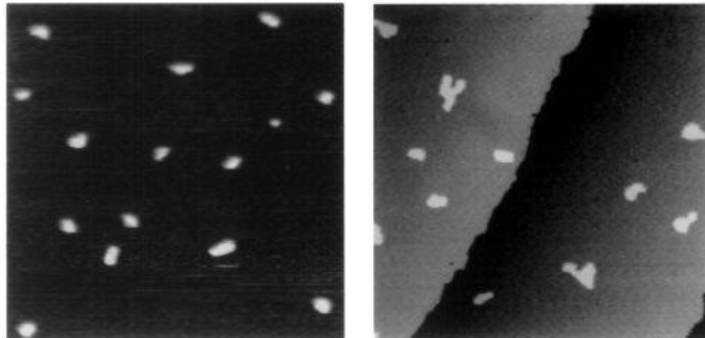
PLATFORMS

- Site-controlled quantum dots and quantum device fabrication
- Wafer-scale graphene device fabrication
- GaN-IC power electronic devices and test structures
- Diamond Platform and IISB 4H-SiC Line

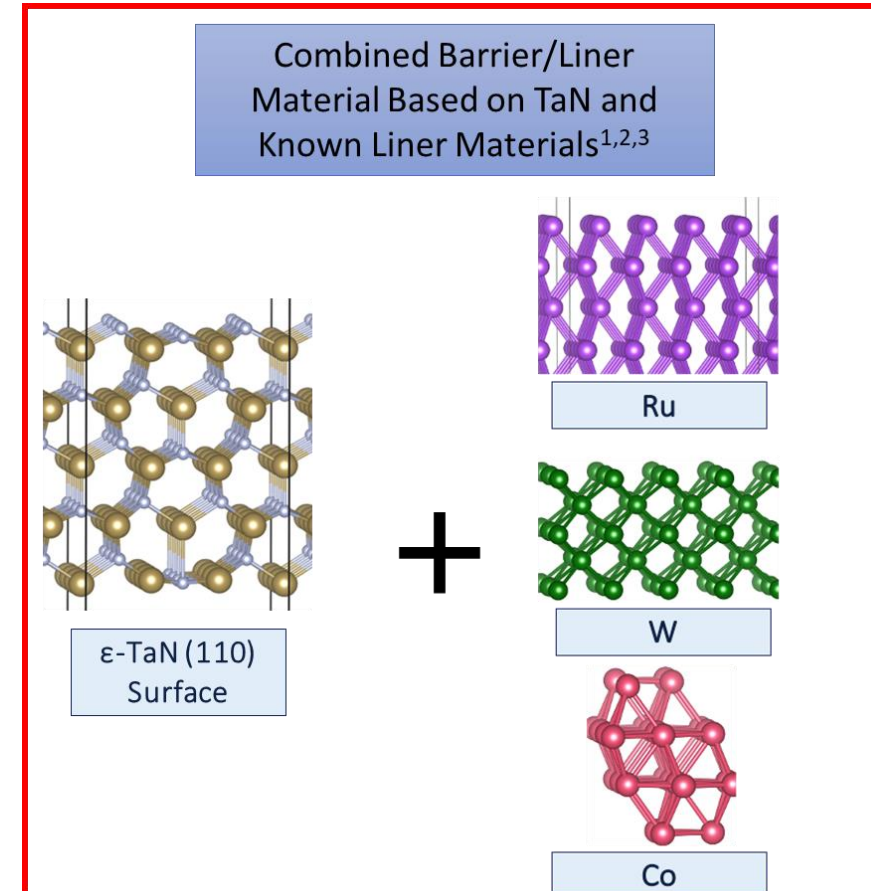
Interconnect Barrier/Liner Challenge



Downscaling Challenges



Copper Islands -> non-conducting

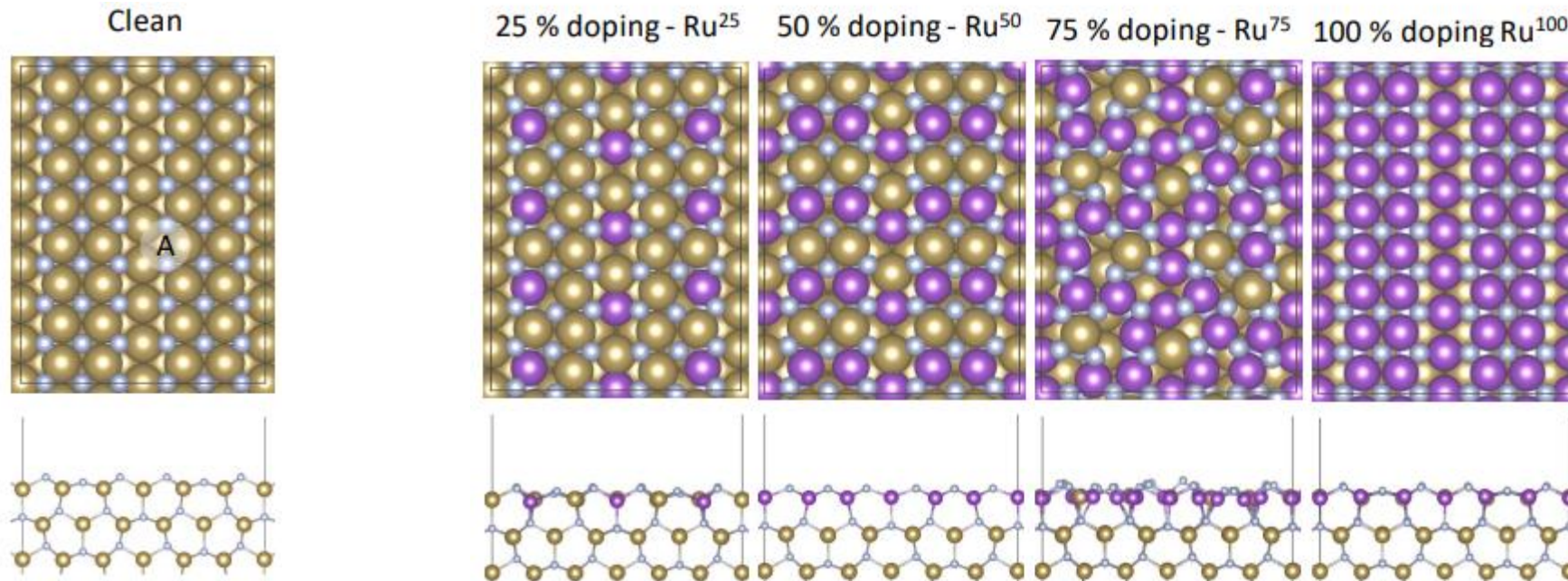
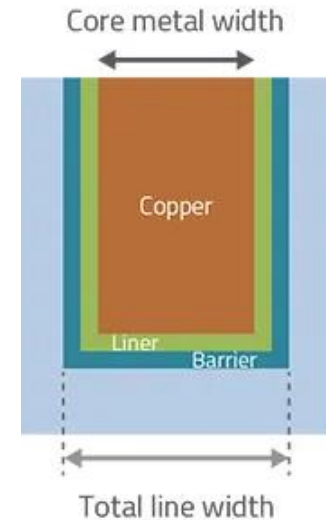


Continue to use Copper – Promoting Deposition of Conducting Copper

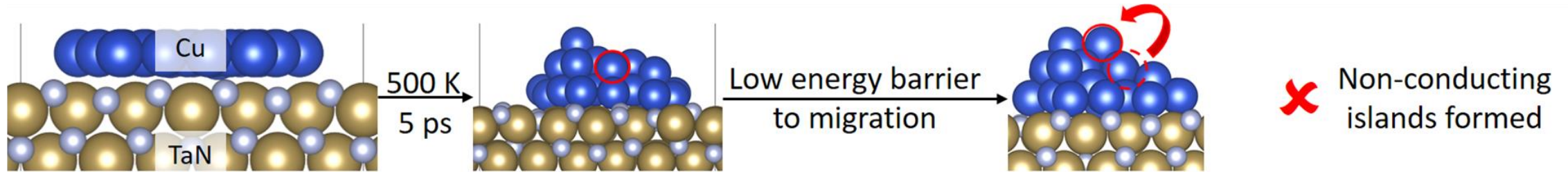
Increase volume available to the metal

Devise new materials system:

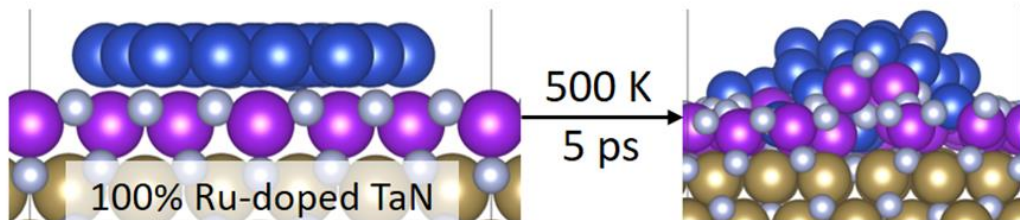
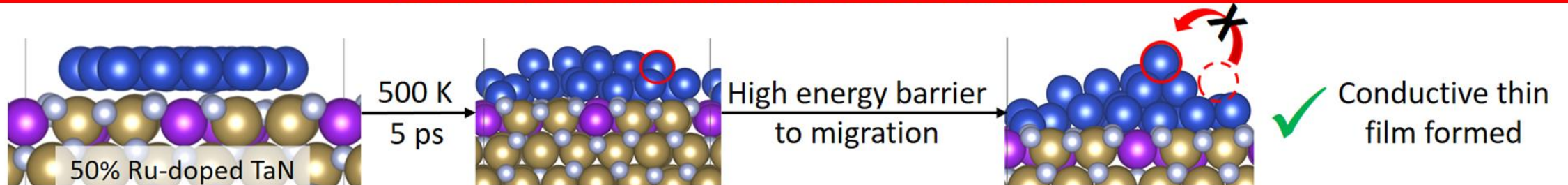
TaN barrier that incorporates Ru directly into its surface layer (using Atomic Layer Deposition)



New Materials to Promote Copper Deposition



50% Ru-doped TaN is a combined barrier/liner material



Thermal
Instability

[Cu-RuTaN morphology paper movies - Google Drive](#)

- 1 - SK Natarajan, [Cara-Lena Nies](#), and M Nolan. J. Mat Chem C (2019) doi:10.1039/C8TC06118A
- 2 - Suresh Kondati Natarajan, Cara-Lena Nies, and Michael Nolan. J. Chem Phys. (2020) doi:10.1063/5.0003852
- 3 - Cara-Lena Nies, Suresh Kondati Natarajan and Michael Nolan. Chem Sci. (2021). doi:10.1039/D1SC04708F